

SEMICONDUCTOR SUBSTRATE AND METHOD OF PRODUCTION

Publication number: JP2001144276 (A)

Publication date: 2001-05-25

Inventor(s): SATO TSUTOMU; MATSUO MIE; MIZUSHIMA ICHIRO;
TSUNASHIMA YOSHITAKA; TAKAGI SHINICHI +

Applicant(s): TOSHIBA CORP +

Classification:

- international: G02B6/10; G02B6/12; G02B6/122; H01L21/00; H01L21/336; more >>

H01L21/78; H01L21/762; H01L21/764; H01L21/822;
H01L21/8238; H01L21/8242; H01L21/84; H01L27/04;
H01L27/08; H01L27/092; H01L27/10; H01L27/108;
H01L27/12; H01L29/06; H01L29/78; H01L29/786;
H01L29/84; G02B6/10; G02B6/12; G02B6/122; H01L21/00;
H01L21/02; H01L21/70; H01L27/04; H01L27/08;
H01L27/085; H01L27/10; H01L27/108; H01L27/12;
H01L29/02; H01L29/66; (IPC1-7): G02B6/122; H01L21/336;
H01L21/762; H01L21/822; H01L21/8242; H01L27/04;
H01L27/092; H01L27/12; H01L29/786; H01L29/84

- European: G02B6/122; G02B6/122P; H01L21/762D20M;
H01L21/762D26P; H01L21/764; H01L21/8242P; H01L21/84;
H01L27/108F; H01L27/108P; H01L27/12B; H01L29/06C;
H01L29/786A; H01L29/786B7; Y01N10/00

Application number: JP20000252881 20000823

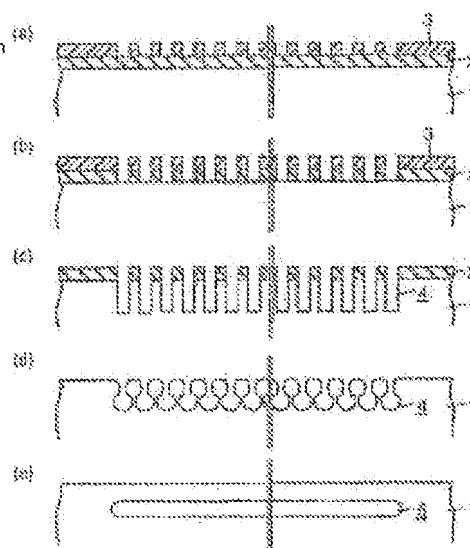
Priority number(s): JP20000252881 20000823; JP19990246582 19990831

Also published as:

JP4074051 (B2)
US7019364 (B1)
US2006131651 (A1)
US7235456 (B2)
KR20010030200 (A)

Abstract of JP 2001144276 (A)

PROBLEM TO BE SOLVED: To form an SOI structure without causing cost increase or lowering of reliability. SOLUTION: A plurality of grooves 4 are made in the surface of a silicon substrate 1 while being arranged two-dimensionally and then the silicon substrate 1 is heat treated to deform the plurality of grooves 4 into one planar cavity 5.



Data supplied from the *espacenet* database — Worldwide